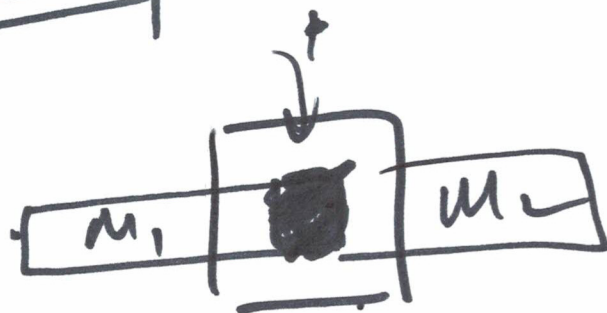
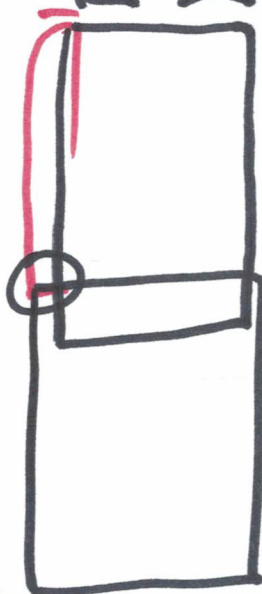
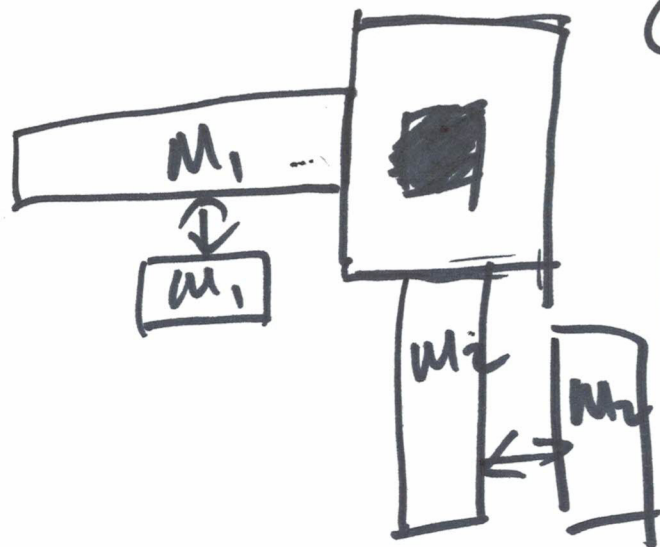
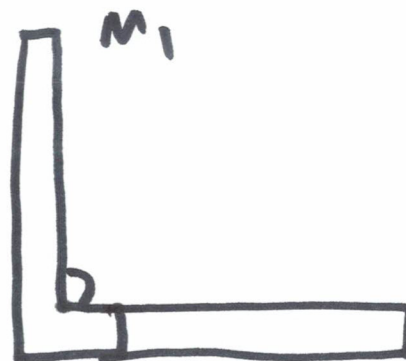
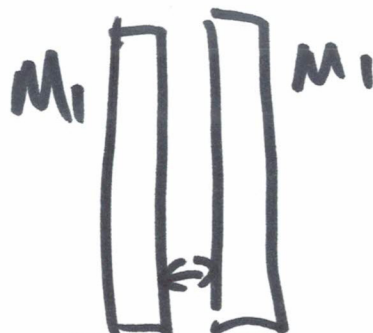




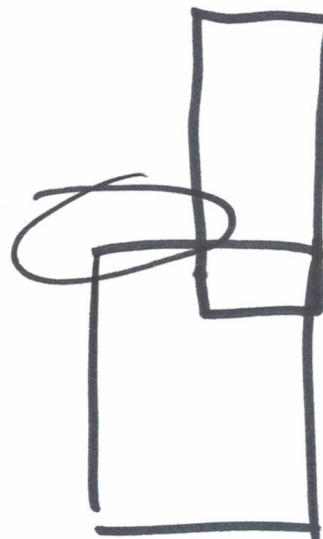
left click



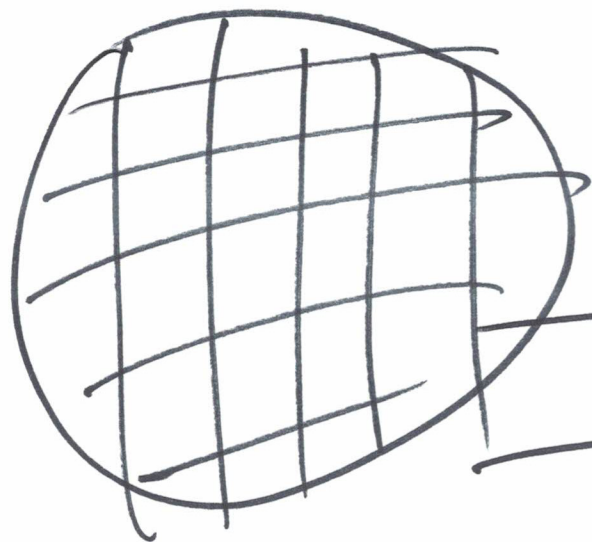
DRC



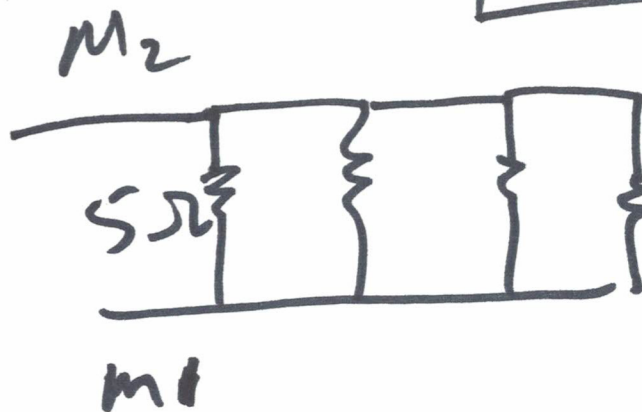
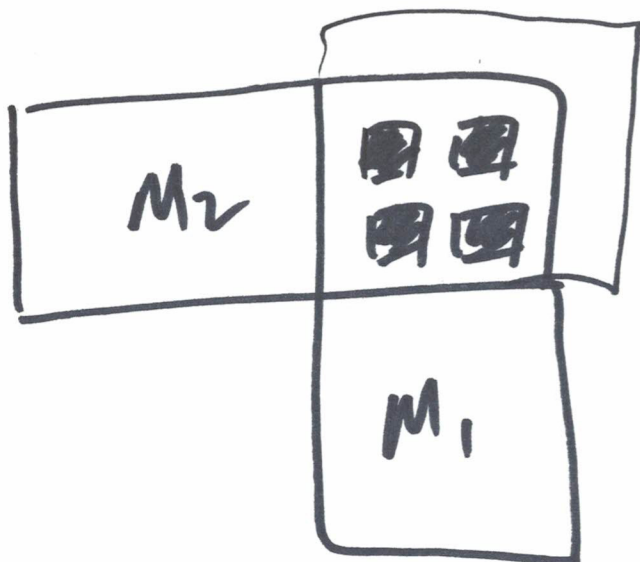
M1



①

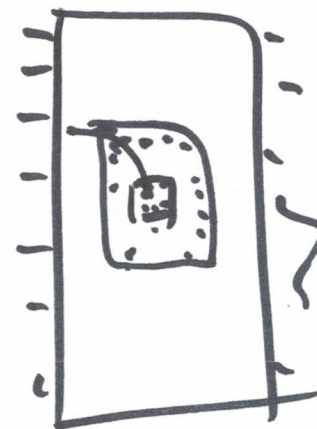


yield



Passivation

DIP-40



(3)

efabless

Poly used as resistors and capacitors

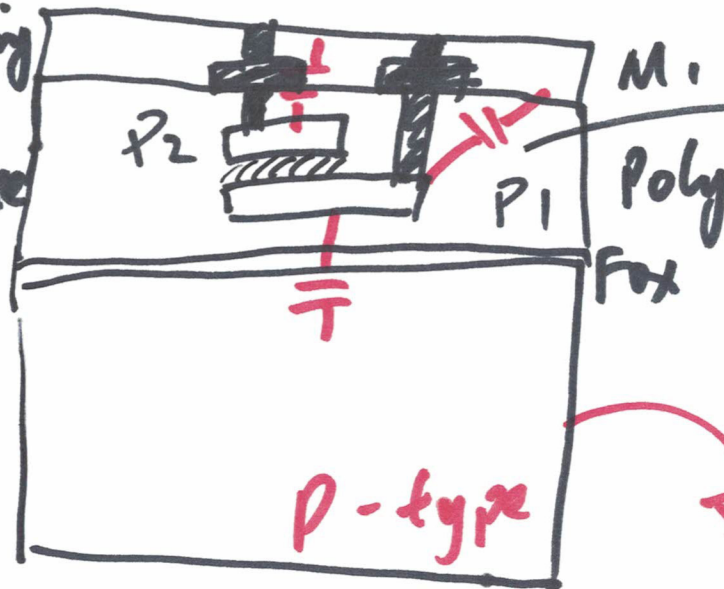


	Resistance
Poly	200 $\Omega/\square$
Metal	0.1 $\Omega/\square$

$$C = \epsilon \frac{A}{d}$$

$A \rightarrow$ area

$d \rightarrow$ distance



insulator
largest undesired:
poly to sub
parasitic
capacitance.

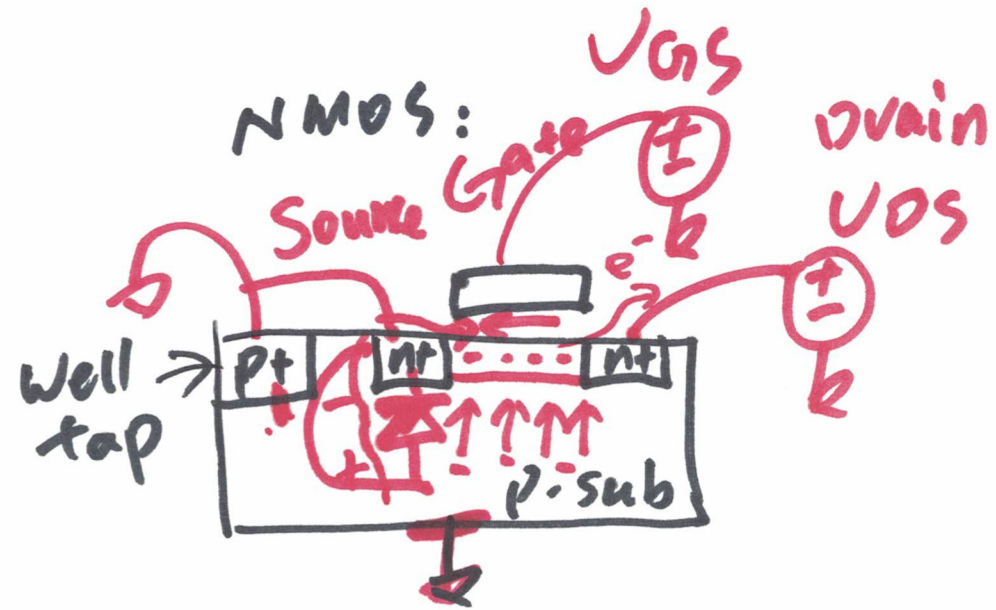
MOSFET: Metal Oxide Semiconductor Field Effect Transistor

~~✗~~
NMOS
N-type

PMOS
P-type


NMOS


PMOS



NMOS is in
the p-well

Body-Effect

(4)

